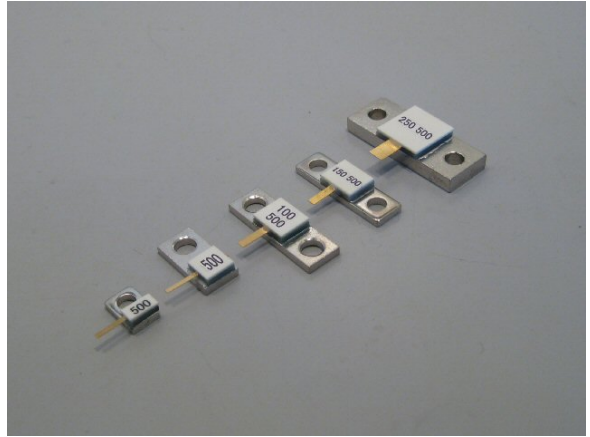


10W, 50W, 80W, 100W, 150W, 200W
250W
FLANGED POWER TERMINATIONS, RFT



Features:

- High power flanged termination for all DC up to 4GHz applications.
- Small size and wide frequency range specifications realized with through large heat conducting AlN substrate.
- Sufficient mechanical strength metallization from spattered thin film technology.
- 50ohm resistance with tolerance 1%, and terminations include chips and many style flange provided as standard, and other resistance and power available.
- Long life and temperature stability are shown by a result of Ni-Cr thin film technology.

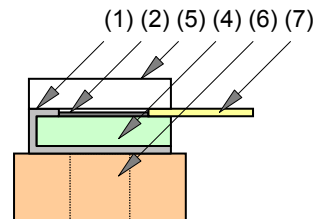
Applications: Termination for isolator/circulators, Fixed station of mobile communication electronics, High power microwave amplifiers

Ordering Information

Type RFT050	Style 120	TCR C	Resistance 500	Tolerance F	RoHS/Package Z00
RFT010	100	C (50ppm)	50 Ohm	F (1.0%)	Z00
RFT050	110				
RFT080	120				
RFT100	130				
RFT150	140				
RFT200					
RFT250					

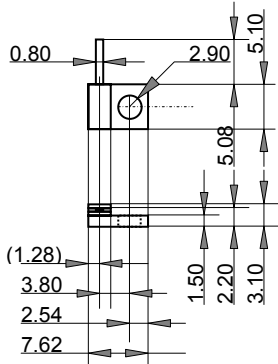
Performance Specifications

Type	Rated Power (W)	Heat Resistance (deg C/W)	VSWR 500MHz	VSWR 1GHz	VSWR 2GHz
RFT010	10	6.5	---	1.15	---
RFT050	50	2.5	---	1.15	---
RFT080	80	---	---	1.20	---
RFT100	100	1.3	---	1.20	---
RFT150	150	---	---	1.30	---
RFT200	200	---	---	1.30	---
RFT250	250	0.5	---	1.30	---

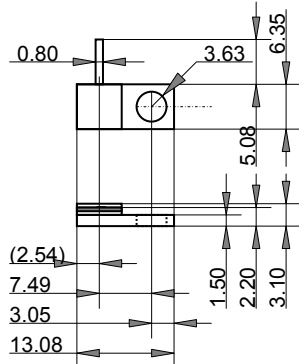


	Substance	Material
(1)	Cold end Terminal	Tin plated Ni-Cu
(2)	Resistive	Ni-Cr
(3)	Substrate	ALN
(4)	Hot end Terminal	Tin plated Ni-Cu
(5)	Cover	ALO
(6)	Flange	Ni plated Cu
(7)	Beam Lead	Au plated Cu

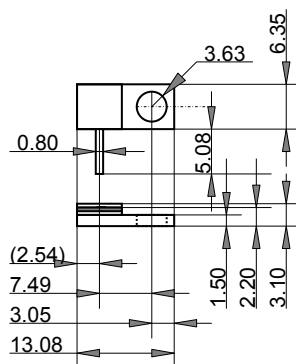
10W, 50W, 80W, 100W, 150W, 200W, 250W, TERMINATIONS RFT
 Style and Dimension (mm)



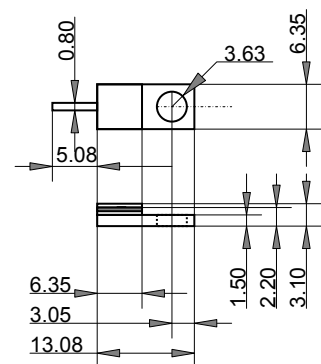
RFT010 120



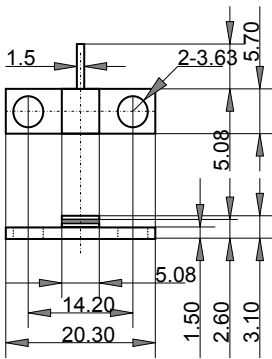
RFT050 120
RFT080 120



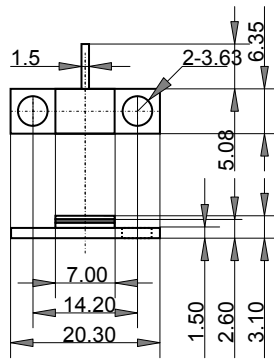
RFT050 130
RFT080 130



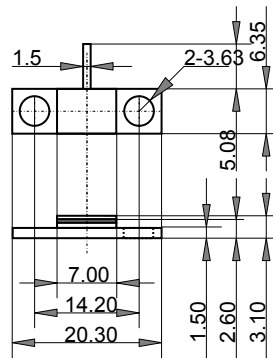
RFT050 140
RFT080 140



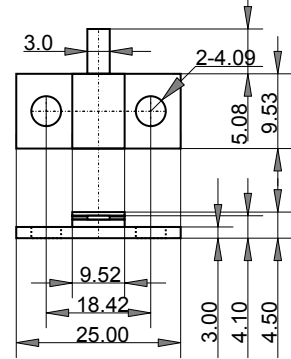
RFT050 110



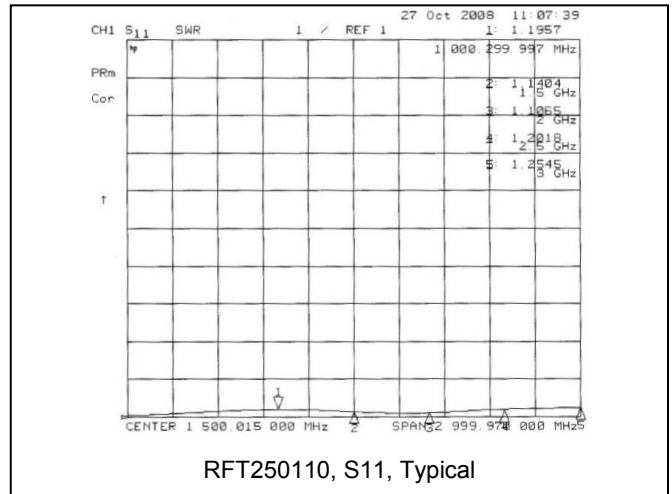
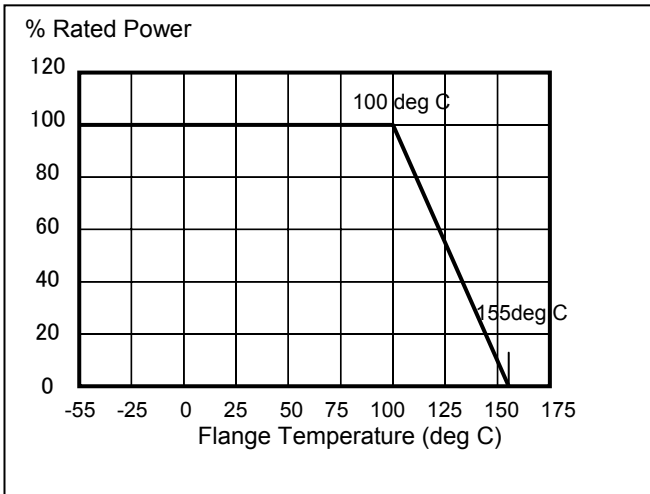
RFT100 110



RFT150 110



RFT250 110



RFT250110, S11, Typical

Note: RoHS 2011/65/EU conformity.
 Country origin, Aomori Pref. Japan